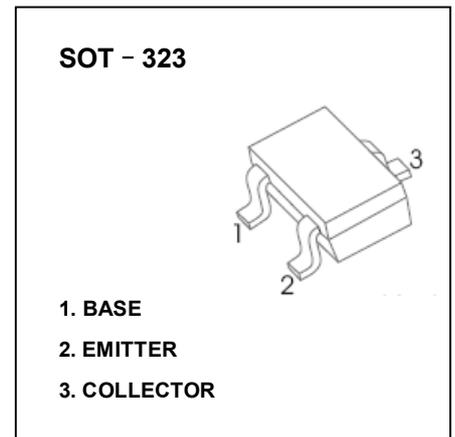


TRANSISTOR(PNP)

FEATURES

- Small Surface Mount Package
- High DC Current Gain



MAXIMUM RATINGS ($T_a=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Value	Unit
V_{CBO}	Collector-Base Voltage	-50	V
V_{CEO}	Collector-Emitter Voltage	-45	V
V_{EBO}	Emitter-Base Voltage	-5	V
I_{C}	Collector Current	-100	mA
P_{C}	Collector Power Dissipation	200	mW
$R_{\theta\text{JA}}$	Thermal Resistance From Junction To Ambient	625	$^{\circ}\text{C}/\text{W}$
T_{J}	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55~+150	$^{\circ}\text{C}$

ELECTRICAL CHARACTERISTICS ($T_a=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(\text{BR})\text{CBO}}$	$I_{\text{C}}=-100\mu\text{A}$, $I_{\text{E}}=0$	-50			V
Collector-emitter breakdown voltage	$V_{(\text{BR})\text{CEO}}$	$I_{\text{C}}=-100\mu\text{A}$, $I_{\text{B}}=0$	-45			V
Emitter-base breakdown voltage	$V_{(\text{BR})\text{EBO}}$	$I_{\text{E}}=-100\mu\text{A}$, $I_{\text{C}}=0$	-5			V
Collector cut-off current	I_{CBO}	$V_{\text{CB}}=-50\text{V}$, $I_{\text{E}}=0$			-100	nA
Emitter cut-off current	I_{EBO}	$V_{\text{EB}}=-5\text{V}$, $I_{\text{C}}=0$			-100	nA
DC current gain	h_{FE}	$V_{\text{CE}}=-5\text{V}$, $I_{\text{C}}=-1\text{mA}$	200		1000	
Collector-emitter saturation voltage	$V_{\text{CE}(\text{sat})}$	$I_{\text{C}}=-100\text{mA}$, $I_{\text{B}}=-10\text{mA}$			-0.3	V
Base-emitter saturation voltage	$V_{\text{BE}(\text{sat})}$	$I_{\text{C}}=-100\text{mA}$, $I_{\text{B}}=-10\text{mA}$			-1	V
Base-emitter voltage	V_{BE}	$V_{\text{CE}}=-5\text{V}$, $I_{\text{C}}=-1\text{mA}$	-0.6		-0.75	V
Transition frequency	f_{T}	$V_{\text{CE}}=-5\text{V}$, $I_{\text{C}}=-10\text{mA}$, $f=30\text{MHz}$	150			MHz
Collector output capacitance	C_{ob}	$V_{\text{CB}}=-10\text{V}$, $I_{\text{E}}=0$, $f=1\text{MHz}$			7	pF

CLASSIFICATION OF h_{FE}

RANK	L	H
RANGE	200 - 450	450 - 1000
MARKING	FR	

Typical Characteristics
